Attorney Docket No. 033035 M 0342

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re tl	ne application of:	)	CONFIRM	IATION NO.: 6958
	Kensaku MOTOKI, et al.	)		
U.S. S	erial No.: 10/691,569	)	Group Art I	Jnit: 2814
Filed:	October 24, 2003	)	Examiner:	Marcos D. Pizarro Crespo
For:	GaN SINGLE CRYSTAL SUBSTR	RATE A	ND METHO	D OF MAKING THE SAME
Sir:				

# FIFTH INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure under 37 C.F.R. 1.56, Applicants enclose an Information Disclosure Citation Form (PTO-1449) and a copy of the documents cited therein. The documents were cited by the Examiner in another Office Action issued for copending Application No. 10/691,540.

It is respectfully requested that the cited documents be considered by the Examiner, that they be made officially of record therein, and that the documents be listed on the face of any patent which may issue from this application. This paper is being submitted with a Request for Continued Examination (RCE) and therefore no fees are considered necessary.

> Respectfully submitted, SMITH, GAMBRELL & RUSSELL, LLP

By:

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Date: July 26, 2007



FORM PTO-1449

## INFORMATION DISCLOSURE STATEMENT

ATTY. DOCKET	SE
033035 M 0342	

SERIAL NO. 10/691,569

APPLICANTS:

Kensaku MOTOKI, et al.

FILING DATE

GROUP ART UNIT

October 24, 2003 2814

#### U.S. PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE, IF APPROPRIAT
/M.P./	AA	5,828,088	10/27/1998	MAUK			E
8	AB	5,838,029	11/17/1998	SHAKUDA			
	AC	5,679,152	10/21/1997	TISCHLER et al.			
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/M.P./	AE	5,770,887	06/23/1998	TADATOMO et al.			
	AF						
	AG						

#### FOREIGN PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLAS S	TRANSLATI YES	NO NO
	АН							
	Al							
	AJ		,					
	AK							

OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

/M.P./	AL	Office Action for U. S. Patent Application No. 10/691,540 dated April 5, 2005.
/M.P./	AM	IBM, Abstract of "Method of Producing Gallium Nitride Boules for Processing into Substrates," IBM Technical Disclosure Bullet May 1997, Vol 40, Issue 5, May 1, 1997.
/M.P./	AN	Zheleva et al. "Dislocation density reduction via lateral epitaxy in selectively grown GaN structures," Appl. Phys. Lett. 71 (17) 27 October 1997, pp 2472-2474.
/M.P./	AO	Nam et al. "Lateral epitaxy of low defect density GaN layers via organometallic vapor phase epitaxy," Appl. Phys. Lett. 71 (18), 3 November 1997, pp. 2638-2640.
	AP	
	AQ	

EXAMINER:

/Marcos Pizarro Crespo/

DATE CONSIDERED:

08/04/2007

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.